

30V N-Channel MOSFETs

General Description

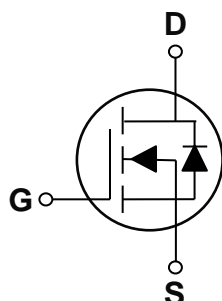
These N-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

BVDSS	RDSON	ID
30V	2.4mΩ	115A

Features

- 30V, 115A, $R_{DS(ON)} = 2.4m\Omega @ V_{GS} = 10V$
- Improved dv/dt capability
- Fast switching
- 100% EAS Guaranteed
- Green Device Available

PPAK5x6 Pin Configuration



Applications

- MB / VGA / Vcore
- POL Applications
- SMPS 2nd SR

Absolute Maximum Ratings $T_c=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current – Continuous ($T_c=25^\circ\text{C}$)	115	A
	Drain Current – Continuous ($T_c=100^\circ\text{C}$)	72	A
I_{DM}	Drain Current – Pulsed ¹	460	A
EAS	Single Pulse Avalanche Energy ²	180	mJ
IAS	Single Pulse Avalanche Current ²	60	A
P_D	Power Dissipation ($T_c=25^\circ\text{C}$)	135	W
	Power Dissipation – Derate above 25°C	1.08	W/ $^\circ\text{C}$
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	62	$^\circ\text{C}/\text{W}$
$R_{\theta JC}$	Thermal Resistance Junction to Case	---	0.92	$^\circ\text{C}/\text{W}$



FTK3960DFN56

30V N-Channel MOSFETs

Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	30	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BV_{DSS} Temperature Coefficient	Reference to 25°C , $I_D=1\text{mA}$	---	0.03	---	$V/^\circ\text{C}$
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=30V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	1	μA
		$V_{DS}=24V, V_{GS}=0V, T_J=125^\circ\text{C}$	---	---	10	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA

On Characteristics

$R_{DS(ON)}$	Static Drain-Source On-Resistance ³	$V_{GS}=10V, I_D=30A$	---	1.9	2.4	m Ω
		$V_{GS}=4.5V, I_D=15A$	---	2.5	3.3	m Ω
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\mu A$	1.2	1.6	2.5	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-5	---	mV/ $^\circ\text{C}$
gfs	Forward Transconductance	$V_{DS}=10V, I_D=2A$	---	16.5	---	S

Dynamic Characteristics

Q_g	Total Gate Charge ^{3, 4}	$V_{DS}=15V, V_{GS}=4.5V, I_D=24A$	---	40	75	nC
Q_{gs}	Gate-Source Charge ^{3, 4}		---	6	12	
Q_{gd}	Gate-Drain Charge ^{3, 4}		---	19	35	
$T_{d(on)}$	Turn-On Delay Time ^{3, 4}	$V_{DD}=15V, V_{GS}=10V, R_G=1\Omega$ $I_D=1A$	---	20	40	ns
T_r	Rise Time ^{3, 4}		---	32	60	
$T_{d(off)}$	Turn-Off Delay Time ^{3, 4}		---	75	130	
T_f	Fall Time ^{3, 4}		---	28	55	
C_{iss}	Input Capacitance	$V_{DS}=25V, V_{GS}=0V, F=1\text{MHz}$	---	4800	8000	pF
C_{oss}	Output Capacitance		---	735	1300	
C_{riss}	Reverse Transfer Capacitance		---	420	800	
R_g	Gate resistance	$V_{GS}=0V, V_{DS}=0V, F=1\text{MHz}$	---	1.6	3.5	Ω

Drain-Source Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	$V_G=V_D=0V$, Force Current	---	---	115	A
I_{SM}	Pulsed Source Current ³		---	---	230	A
V_{SD}	Diode Forward Voltage ³	$V_{GS}=0V, I_S=1A, T_J=25^\circ\text{C}$	---	---	1	V
t_{rr}	Reverse Recovery Time	$V_{DS}=30V, I_S=1A, di/dt=100A/\mu s$	---	49	85	ns
Q_{rr}	Reverse Recovery Charge	$T_J=25^\circ\text{C}$	---	18	35	nC

Note :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. $V_{DD}=25V, V_{GS}=10V, L=0.1\text{mH}, I_{AS}=60A, R_G=25\Omega$, Starting $T_J=25^\circ\text{C}$.
3. The data tested by pulsed, pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
4. Essentially independent of operating temperature.

30V N-Channel MOSFETs

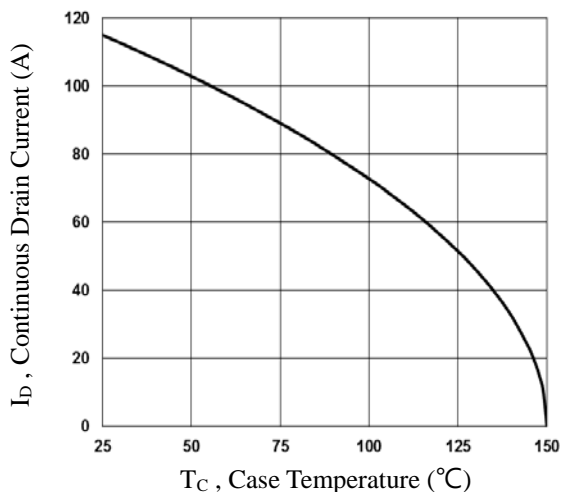


Fig.1 Continuous Drain Current vs. T_C

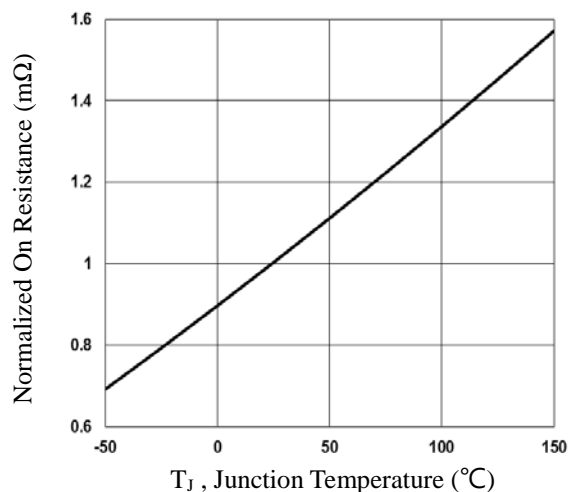


Fig.2 Normalized $R_{DS(on)}$ vs. T_J

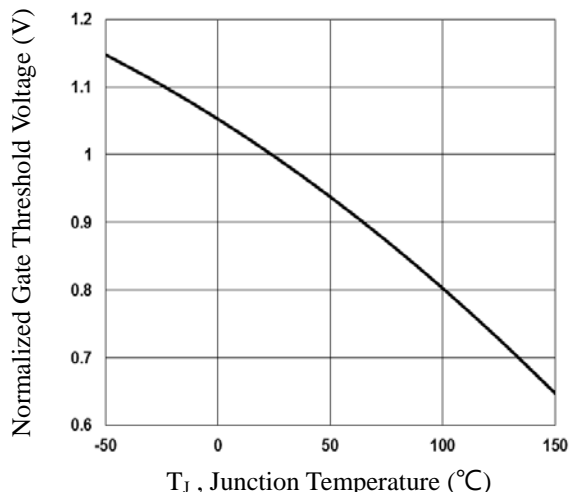


Fig.3 Normalized V_{th} vs. T_J

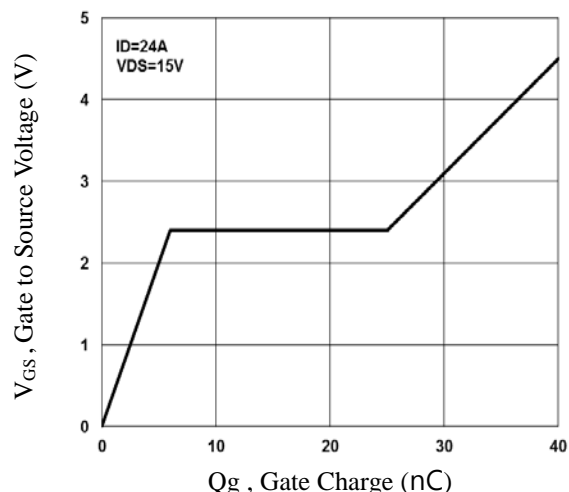


Fig.4 Gate Charge Waveform

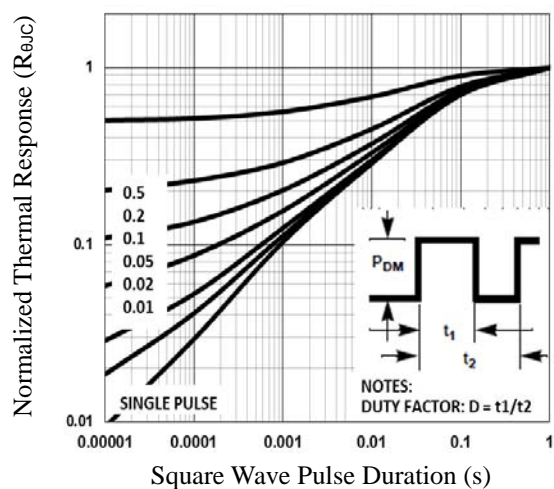


Fig.5 Normalized Transient Impedance

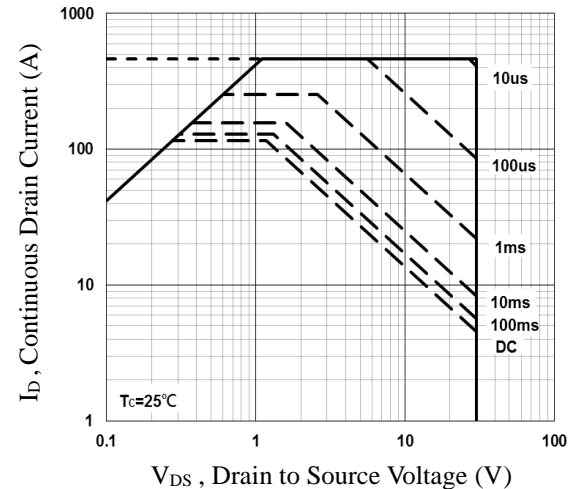


Fig.6 Maximum Safe Operation Area

30V N-Channel MOSFETs

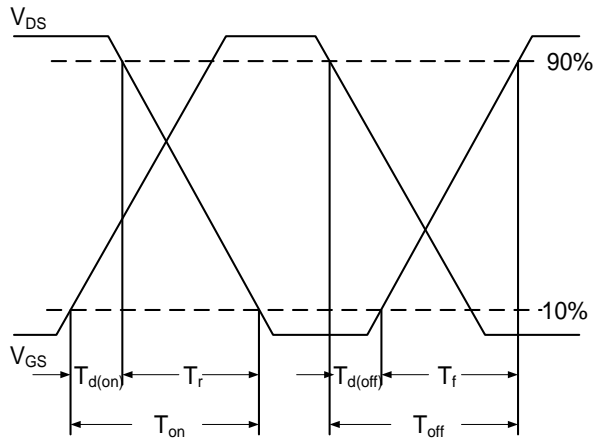


Fig.7 Switching Time Waveform

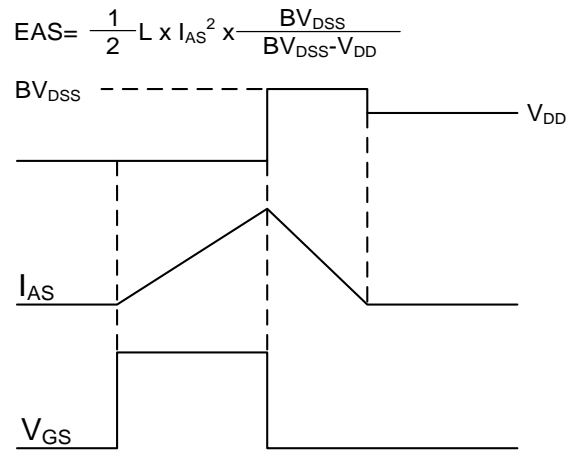
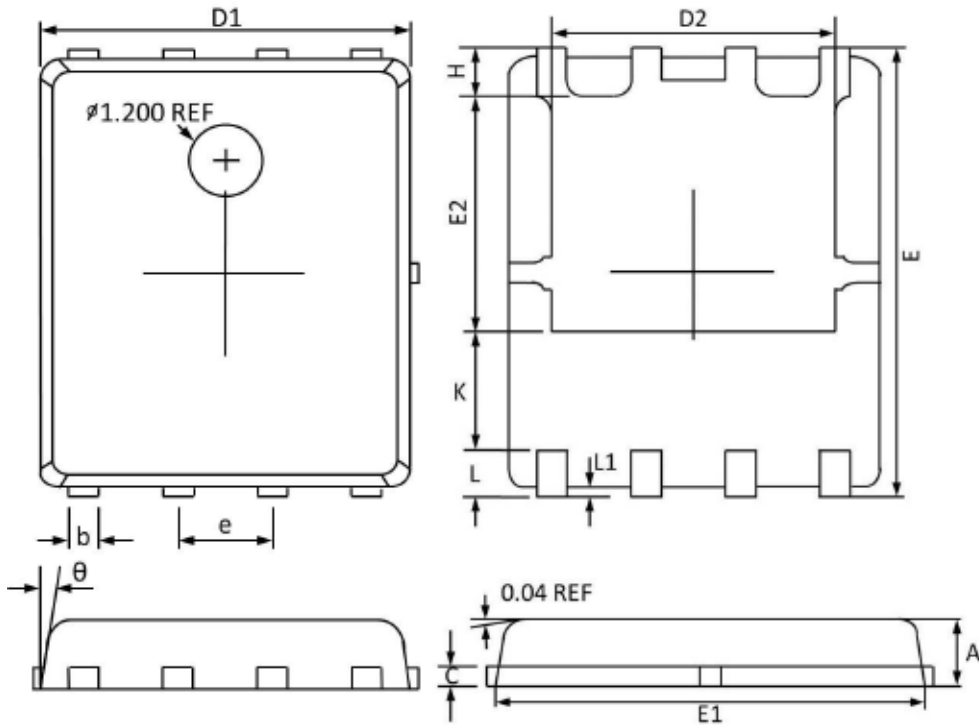


Fig.8 EAS Waveform

30V N-Channel MOSFETs

PPAK5x6 PACKAGE INFORMATION



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MAX	MIN	MAX	MIN
A	1.100	0.800	0.043	0.031
b	0.510	0.330	0.020	0.013
C	0.300	0.200	0.012	0.008
D1	5.100	4.800	0.201	0.189
D2	4.100	3.610	0.161	0.142
E	6.200	5.900	0.244	0.232
E1	5.900	5.700	0.232	0.224
E2	3.780	3.350	0.149	0.132
e	1.27BSC		0.05BSC	
H	0.700	0.410	0.028	0.016
K	1.500	1.100	0.059	0.043
L	0.710	0.510	0.028	0.020
L1	0.200	0.060	0.008	0.002
θ	12°	0°	12°	0°